

MOS FIELD EFFECT TRANSISTOR μ PA1874B

N-CHANNEL MOS FIELD EFFECT TRANSISTOR FOR SWITCHING

DESCRIPTION

The μ PA1874B is a switching device, which can be driven directly by a 2.5 V power source.

The μ PA1874B features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as power switch of portable machine and so on.

FEATURES

- 2.5 V drive available
- · Low on-state resistance

 $R_{DS(on)1} = 14.0 \text{ m}\Omega \text{ MAX.} \text{ (Vgs} = 4.5 \text{ V, Ip} = 4.0 \text{ A)}$

 $R_{DS(on)2} = 14.5 \text{ m}\Omega \text{ MAX}. \text{ (Vgs} = 4.0 \text{ V, Ip} = 4.0 \text{ A)}$

 $R_{DS(on)3} = 16.5 \text{ m}\Omega \text{ MAX.} \text{ (Vgs} = 3.1 \text{ V, I}_D = 4.0 \text{ A)}$

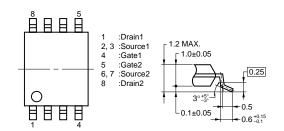
 $R_{DS(on)4}$ = 19.5 m Ω MAX. (Vgs = 2.5 V, ID = 4.0 A)

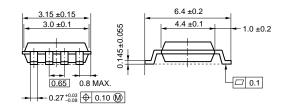
• Built-in G-S protection diode against ESD

ORDERING INFORMATION

PART NUMBER	PACKAGE
μPA1874BGR-9JG	Power TSSOP8

PACKAGE DRAWING (Unit: mm)





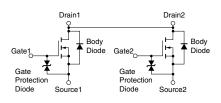
ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Drain to Source Voltage (V _{GS} = 0 V)	Voss	30.0	٧
Gate to Source Voltage (VDS = 0 V)	Vgss	±12.0	V
Drain Current (DC) Note 1	ID(DC)	±8.0	Α
Drain Current (pulse) Note 2	ID(pulse)	±80.0	Α
Total Power Dissipation Note 1	Рт	2.0	W
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	-55 to +150	°C

Notes 1. Mounted on ceramic board of 50 cm² x 1.1 mm

2. PW \leq 10 μ s, Duty Cycle \leq 1%

EQUIVALENT CIRCUIT



The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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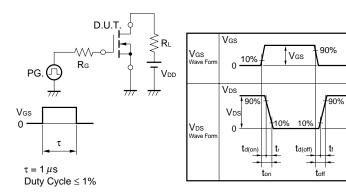
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ELECTRICAL CHARACTERISTICS (TA = 25°C)

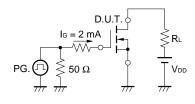
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	IDSS	V _{DS} = 30.0 V, V _{GS} = 0 V			1.0	μΑ
Gate Leakage Current	Igss	V _{GS} = ±12.0 V, V _{DS} = 0 V			±10.0	μΑ
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = 10.0 V, I _D = 1.0 mA	0.50	1.00	1.50	V
Forward Transfer Admittance Note	y _{fs}	V _{DS} = 10.0 V, I _D = 4.0 A	5			S
Drain to Source On-state Resistance Note	RDS(on)1	V _{GS} = 4.5 V, I _D = 4.0 A	9.0	11.5	14.0	mΩ
	RDS(on)2	V _{GS} = 4.0 V, I _D = 4.0 A	9.5	12.0	14.5	mΩ
	RDS(on)3	V _{GS} = 3.1 V, I _D = 4.0 A	10.0	13.0	16.5	mΩ
	RDS(on)4	V _{GS} = 2.5 V, I _D = 4.0 A	11.0	15.0	19.5	mΩ
Input Capacitance	Ciss	V _{DS} = 10.0 V		930		pF
Output Capacitance	Coss	V _{GS} = 0 V		170		pF
Reverse Transfer Capacitance	Crss	f = 1.0 MHz		120		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = 10.0 V, I _D = 4.0 A		46		ns
Rise Time	tr	V _{GS} = 4.0 V		230		ns
Turn-off Delay Time	t _{d(off)}	R _G = 10 Ω		260		ns
Fall Time	tf			250		ns
Total Gate Charge	QG	V _{DD} = 24.0 V		10.0		nC
Gate to Source Charge	Qgs	V _{GS} = 4.0 V		2.0		nC
Gate to Drain Charge	Q _{GD}	I _D = 8.0 A		4.5		nC
Body Diode Forward Voltage Note	V _{F(S-D)}	IF = 8.0 A, VGS = 0 V		0.82		V
Reverse Recovery Time	trr	IF = 8.0 A, VGS = 0 V		150		ns
Reverse Recovery Charge	Qrr	di/dt = 50 A/μs		80		nC

Note Pulsed: PW \leq 350 μ s, Duty Cycle \leq 2%

TEST CIRCUIT 1 SWITCHING TIME

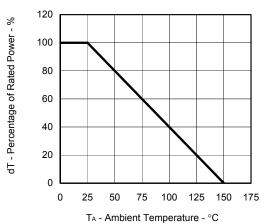


TEST CIRCUIT 2 GATE CHARGE

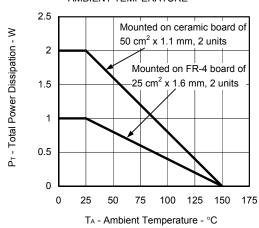


TYPICAL CHARACTERISTICS (TA = 25°C)

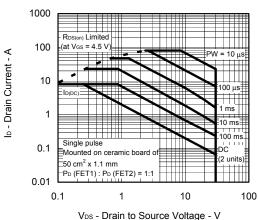
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



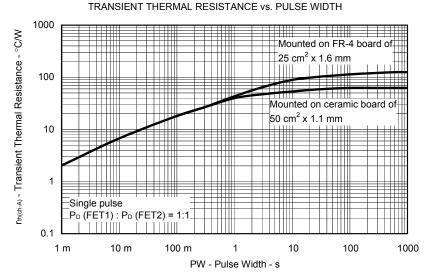
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



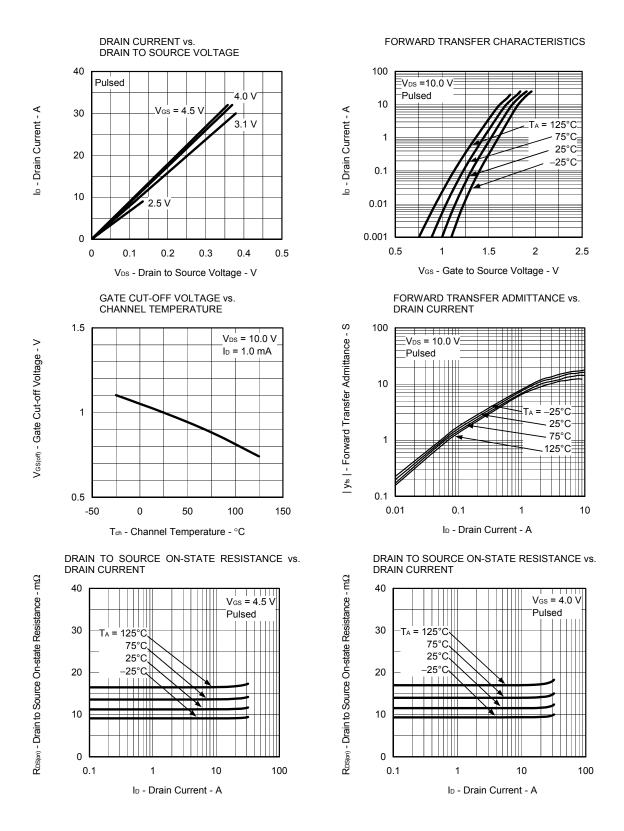
FORWARD BIAS SAFE OPERATING AREA



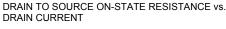


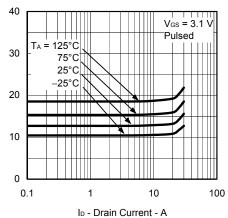


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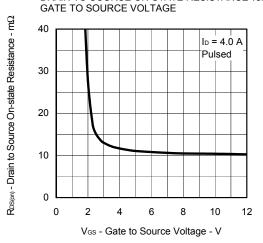


R_{DS(m)} - Drain to Source On-state Resistance - mΩ

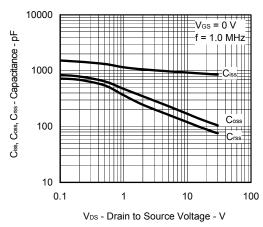




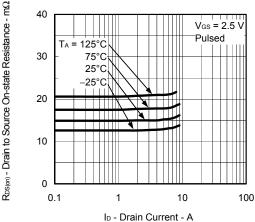
DRAIN TO SOURCE ON-STATE RESISTANCE vs.



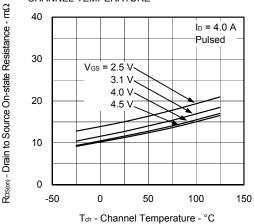
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



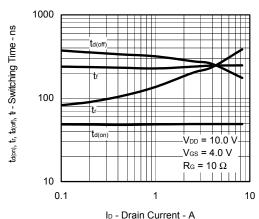
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



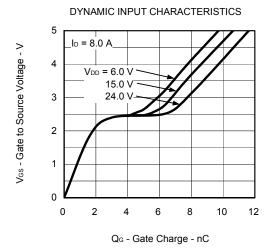
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



SWITCHING CHARACTERISTICS

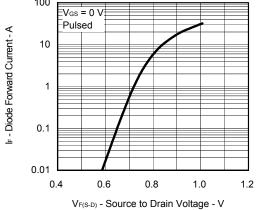


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SOURCE TO DRAIN DIODE FORWARD VOLTAGE



NEC μ PA1874B

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